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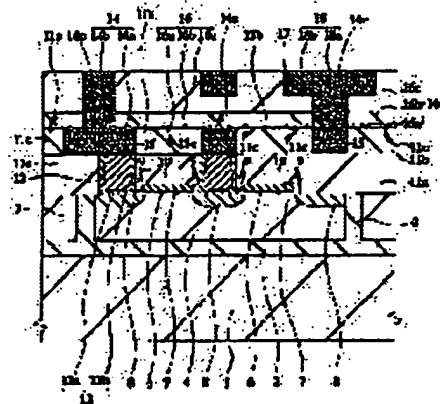
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## (54) SEMICONDUCTOR INTEGRATED CIRCUIT DEVICE AND MANUFACTURE THEREOF

## (57)Abstract:

**PROBLEM TO BE SOLVED:** To increase the yield and the reliability of a semiconductor integrated circuit device by preventing a short-circuit defect of a second metal interconnection formed on a first metal interconnection by CPM(chemical mechanical polishing).

**SOLUTION:** In a semiconductor integrated circuit device, wherein inter-layer insulating films 11a, 11b are formed in an upper part of a semiconductor substrate 1 in which an n-type MISFET Qn is formed, and an interconnection 14 which fills an interconnection recess 14 formed in the interlayer insulating film 11b is formed by depositing a metal film made of copper or the like and polishing it by CMP, an inter-layer insulating film 16 formed on the interconnection 14 and the inter-layer insulating film 11b is constituted of a blocking layer 16a, a planarized layer 16b, and an insulating film 16c. For the planarized layer 16b, a film having a self fluidity such as an SOG(spin-on-glass) film is used.



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